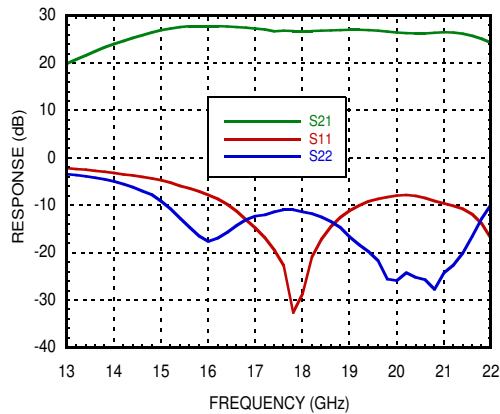
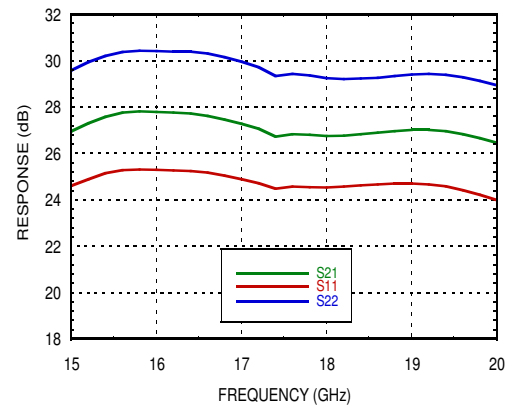


**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 15 - 20 GHz**

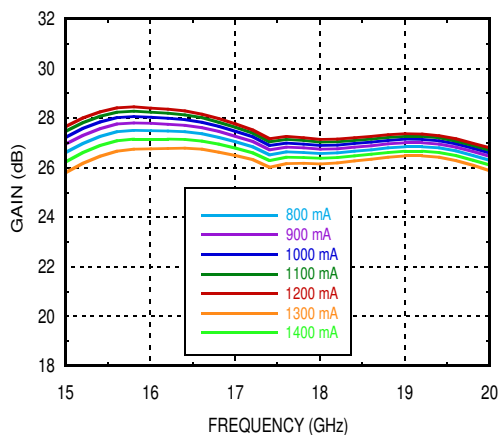
Gain & Return Loss



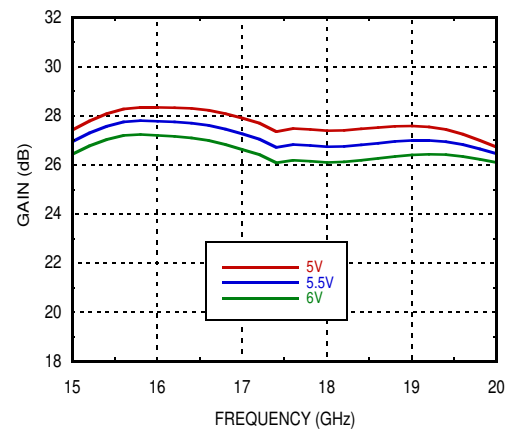
Gain vs. Temperature



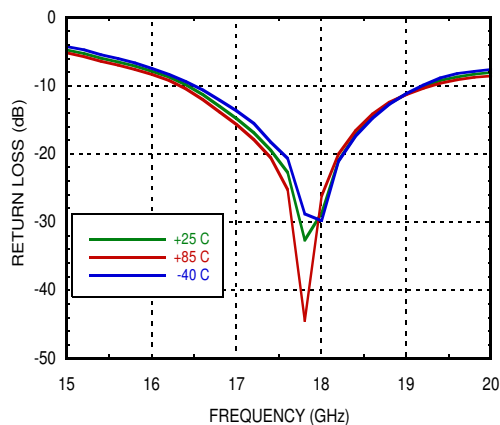
Gain vs. Supply Current



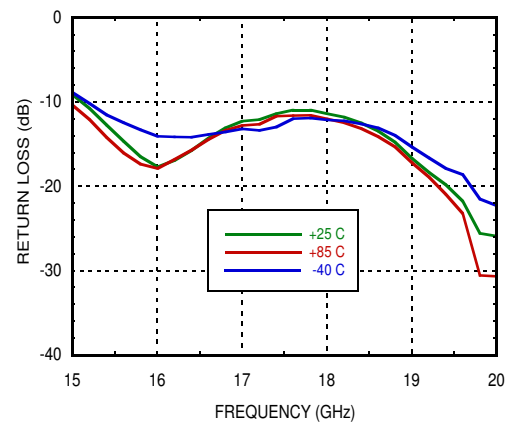
Gain vs. Supply Voltage



Input Return Loss vs. Temperature

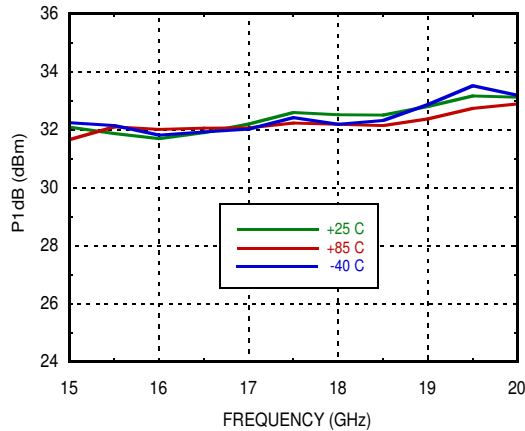


Output Return Loss vs. Temperature

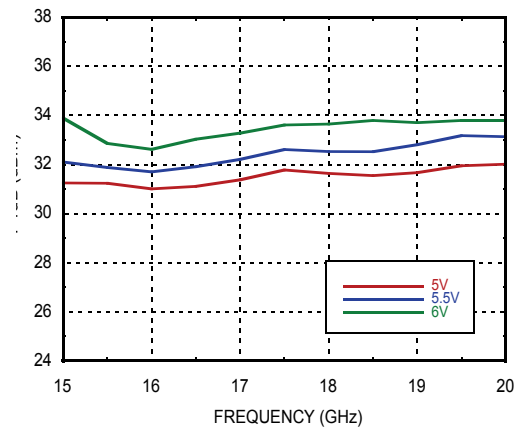


**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 15 - 20 GHz**

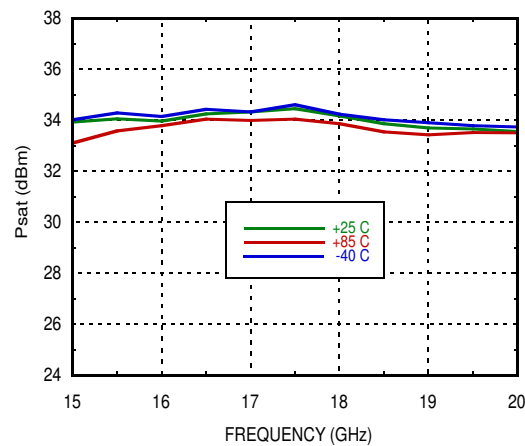
P1dB vs. Temperature



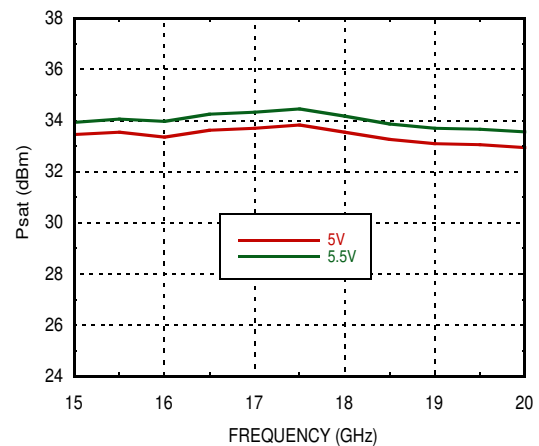
P1dB vs. Supply Voltage



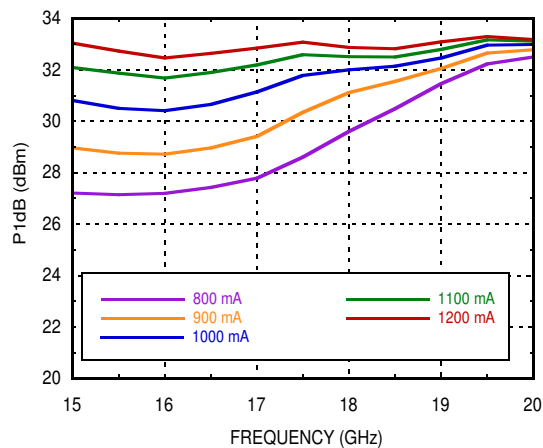
Psat vs. Temperature



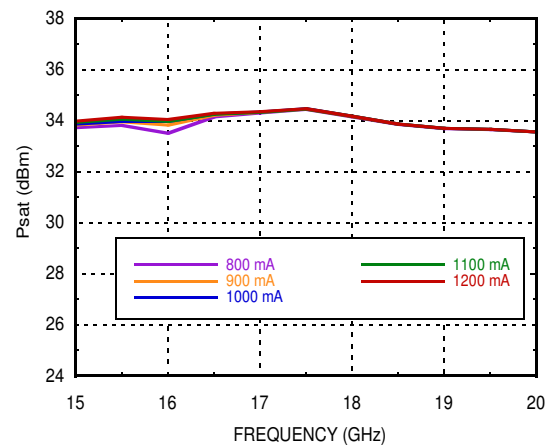
Psat vs. Supply Voltage



P1dB vs. Supply Current

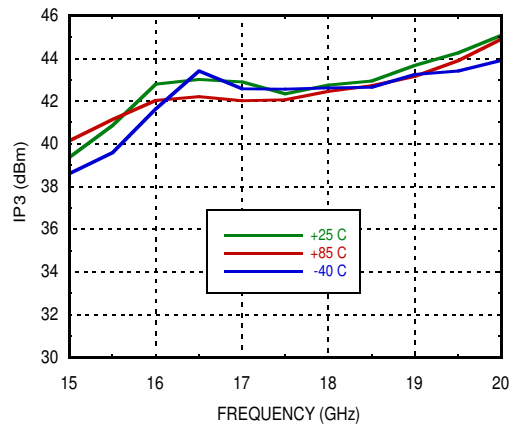


Psat vs. Supply Current

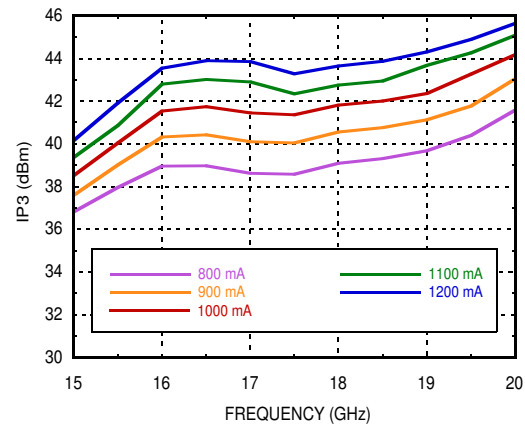


**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 15 - 20 GHz**

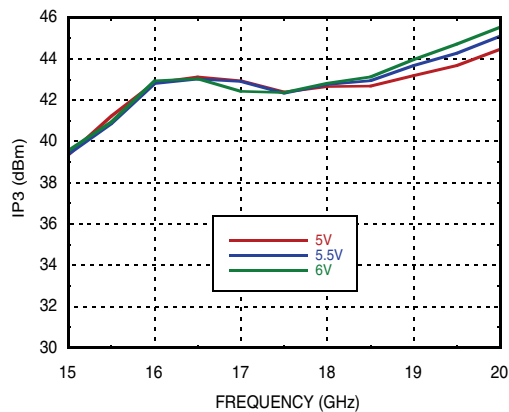
**Output IP3 vs. Temperature,
Pout/tone = +20 dBm**



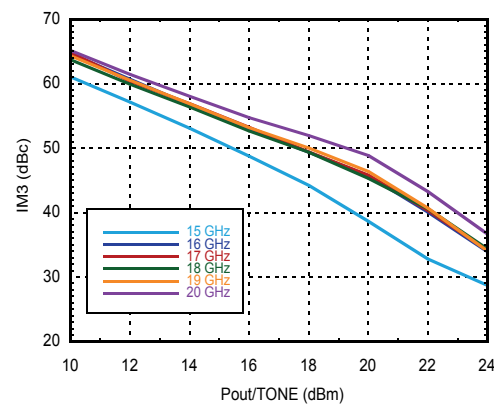
**Output IP3 vs. Supply Current,
Pout/tone = +20 dBm**



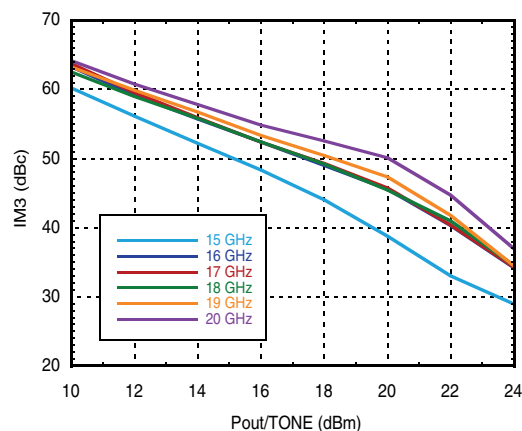
**Output IP3 vs. Supply Voltage,
Pout/tone = +20 dBm**



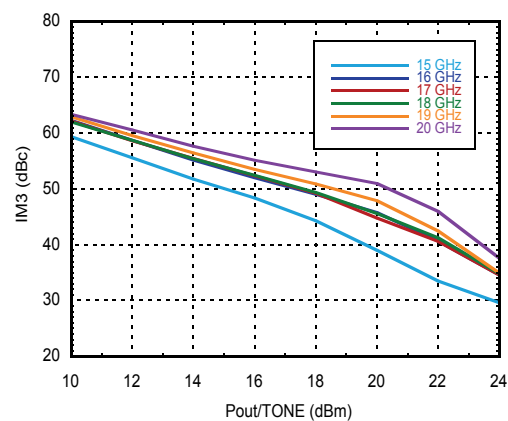
Output IM3 @ Vdd = +5V



Output IM3 @ Vdd = +5.5V

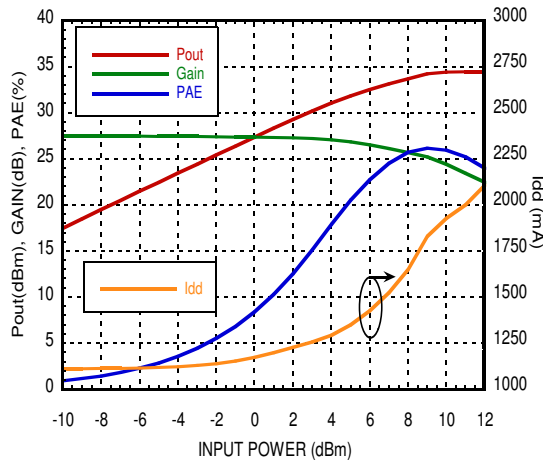


Output IM3 @ Vdd = +6V

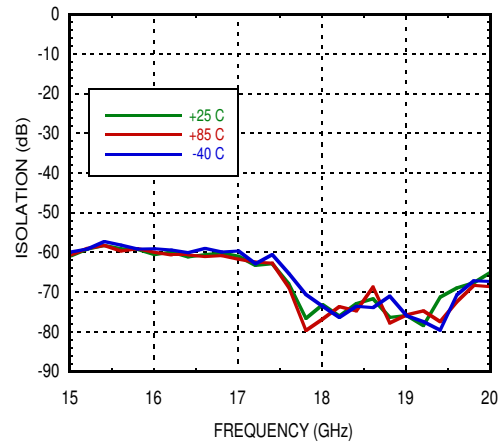


**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 15 - 20 GHz**

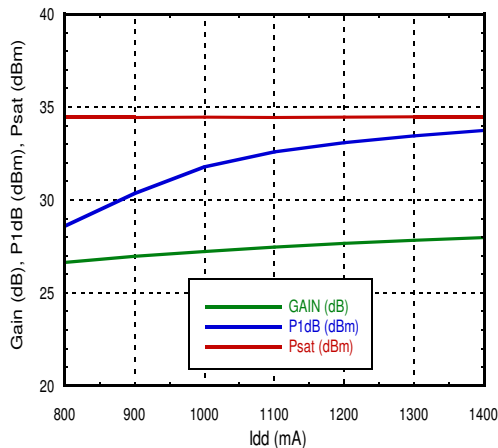
Power Compression @ 17.5 GHz



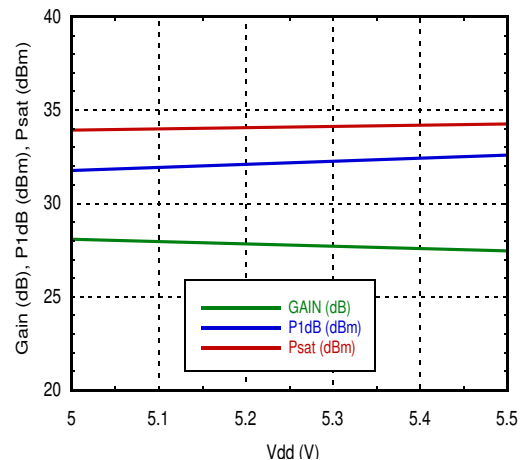
Reverse Isolation vs. Temperature



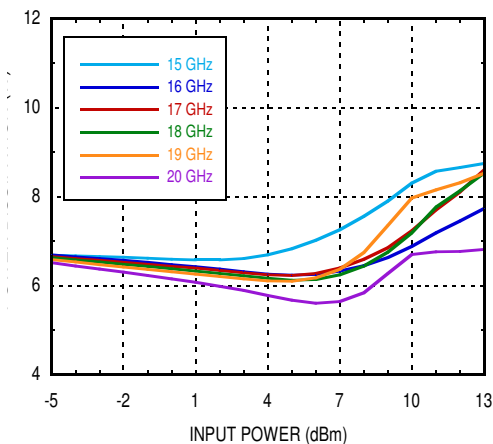
**Gain & Power vs.
Supply Current @ 17.5 GHz**



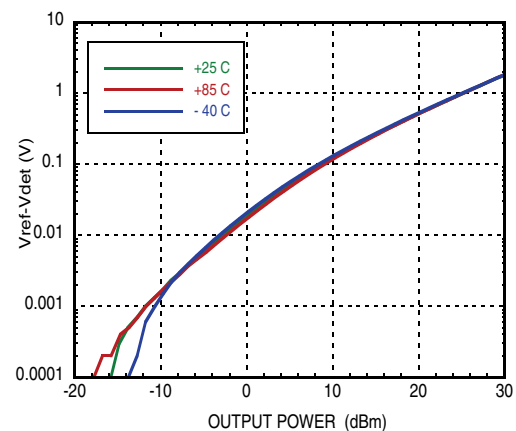
**Gain & Power vs.
Supply Voltage @ 17.5 GHz**



Power Dissipation



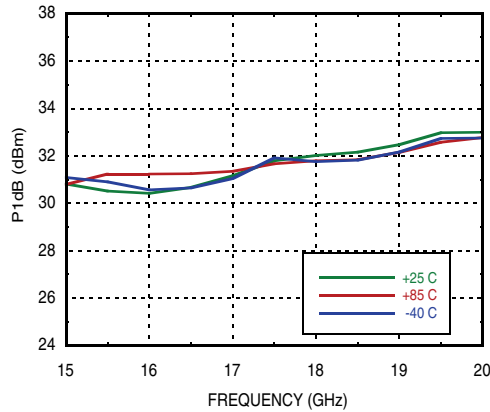
**Detector Voltage vs.
Temperature @ 17.5 GHz**



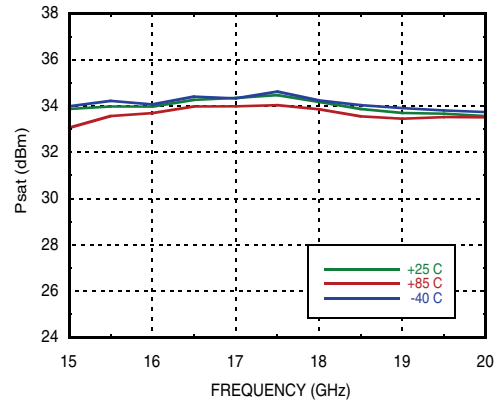
**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 15 - 20 GHz**

Low DC Power Mode, $V_{dd} = 5.5V$, $I_{dd} = 1000\text{ mA}$

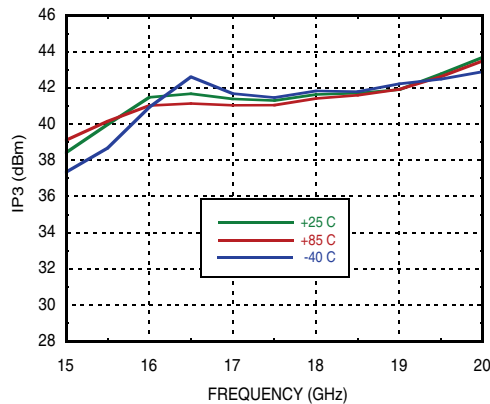
P1dB vs. Temperature



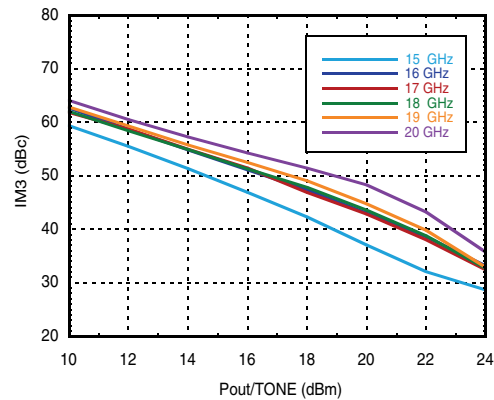
Psat vs. Temperature



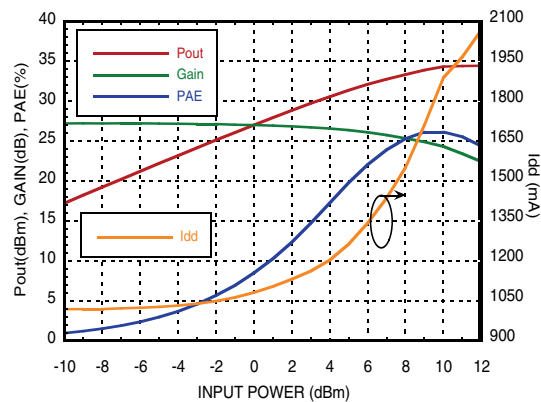
**Output IP3 vs. Temperature,
 $P_{out}/tone = +20\text{ dBm}$**



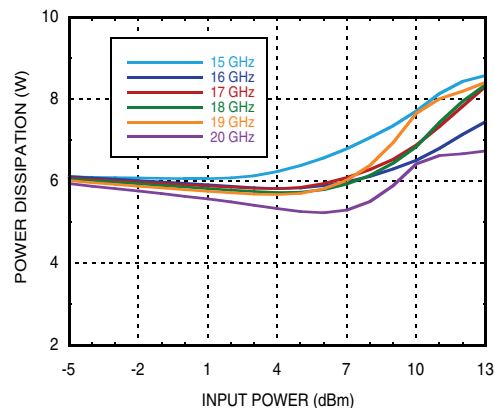
Output IM3 @ $V_{dd} = +5.5V$, 1000 mA



Power Compression @ 17.5 GHz



Power Dissipation





GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 15 - 20 GHz

Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+6.5 Vdc
Gate Bias Voltage (Vgg)	-3 to 0 Vdc
RF Input Power (RFIN)	+18 dBm
Channel Temperature	175 °C
Continuous P _{diss} (T = 85 °C) (derate 129 mW/°C above 85 °C)	11.7 W
Thermal Resistance (channel to ground paddle)	7.7 °C/W
Storage Temperature	-65 to 150 °C
Operating Temperature	-40 to 85 °C
ESD Sensitivity (HBM)	Class 0, Passed 150V

Typical Supply Current vs. Vdd

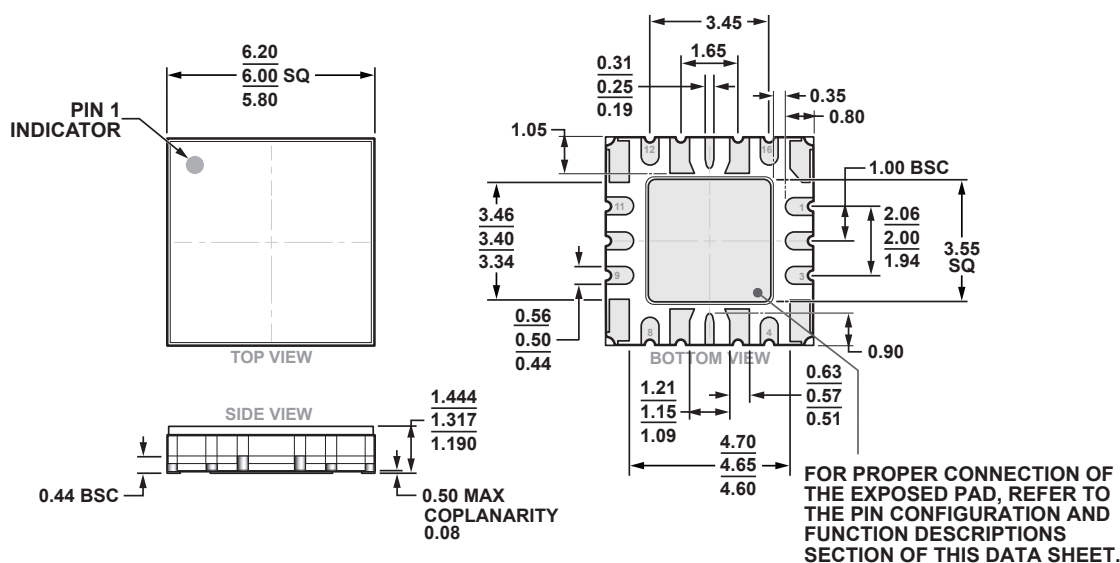
Vdd (V)	Idd (mA)
+5	1100
+5.5	1100
+6	1100

Adjust Vgg to achieve Idd = 1100 mA



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



16-Terminal Ceramic Leadless Chip Carrier with Heat Sink [LCC_HS]
(EP-16-2)

Dimensions shown in millimeters.

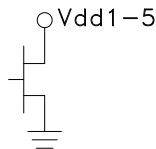
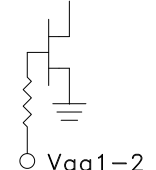
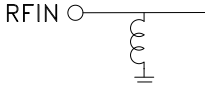
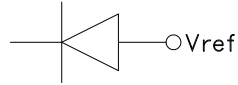
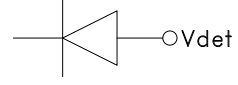
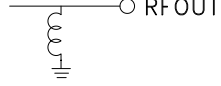
Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating [2]	Package Marking [1]
HMC6981LS6	ALUMINA WHITE	Gold over Nickel	N/A	H6981 XXXX

[1] 4-Digit lot number XXXX

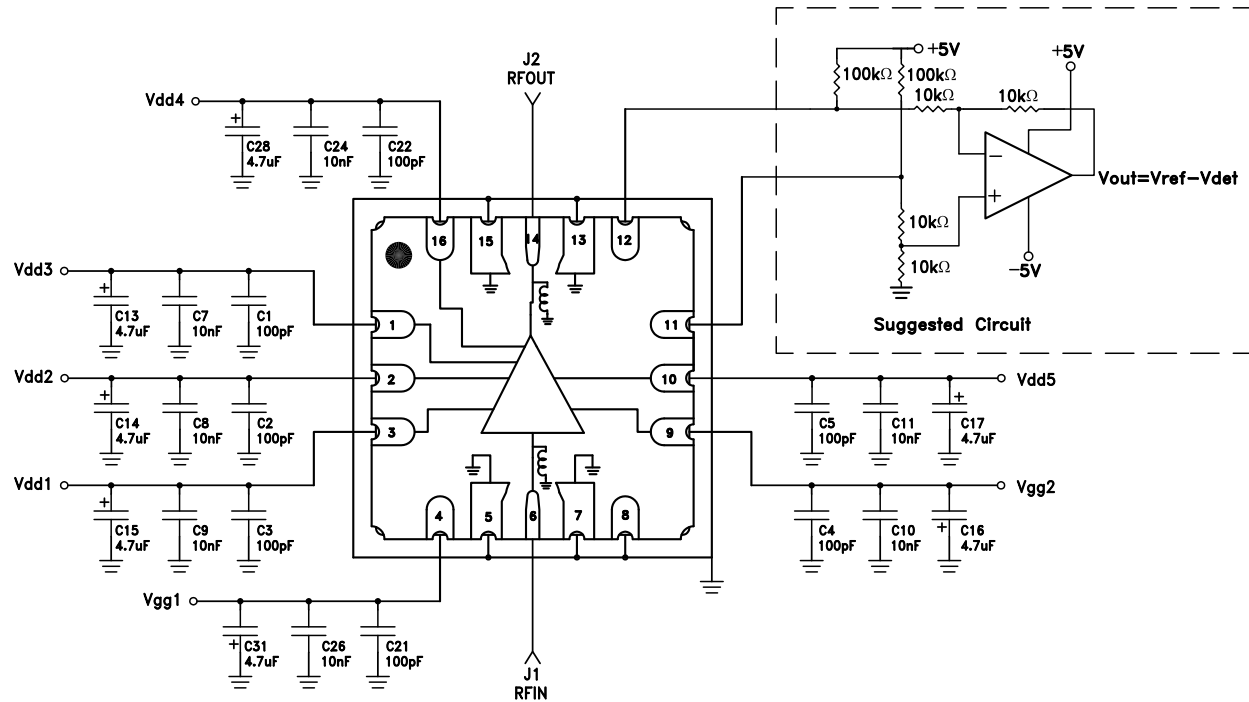
[2] Max peak reflow temperature of 260 °C

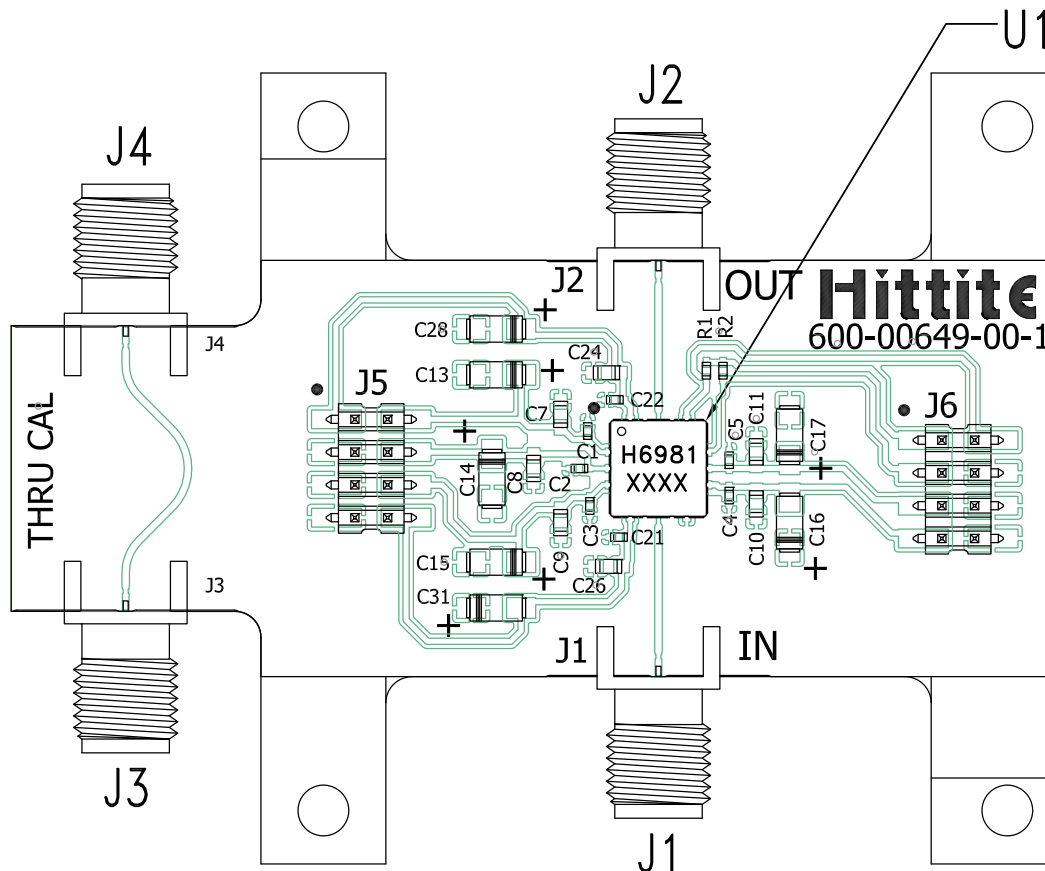
**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 15 - 20 GHz**
Pin Descriptions

Pad Number	Function	Description	Interface Schematic
1, 2, 3, 10, 16	Vdd3, Vdd2, Vdd1, Vdd5, Vdd4	Drain bias voltage. External bypass capacitors of 100 pF, 10 nF, and 4.7 uF are required for each pin.	
4, 9	Vgg1, Vgg2	Gate control for PA. Adjust Vgg to achieve recommended bias current. External bypass capacitors 100 pF, 10 nF, and 4.7 uF are required. Apply Vgg bias to either pin 4 or pin 9.	
5, 7, 13, 15	GND	These pins and exposed ground paddle must be connected to RF/DC ground.	
6	RFIN	This pin is DC coupled and matched to 50 Ohms.	
11	Vref	DC voltage of diode biased through external resistor used for temperature compensation of Vdet. See Application Circuit.	
12	Vdet	DC voltage representing RF output power rectified by diode which is biased through an external resistor. See Application Circuit.	
14	RFOUT	This pin is DC coupled and matched to 50 Ohms.	

**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 15 - 20 GHz**

Application Circuit



**GaAs pHEMT MMIC 2 WATT
POWER AMPLIFIER, 15 - 20 GHz**
Evaluation PCB

List of Materials for Evaluation PCB EVAL01-HMC6981LS6 ^[1]

Item	Description
J1 - J4	"K" Connector, SRI
J5, J6	DC Pin
C1 - C5, C21, C22	100 pF Capacitor, 0402 Pkg.
C7 - C11, C24, C26	10000 pF Capacitor, 0603 Pkg.
C13 - C17, C28, C31	4.7 uF Capacitor, Case A Pkg.
R1, R2	42.6K Ohm Resistor, 0402 Pkg.
U1	HMC6981LS6 Amplifier
PCB ^[2]	600-00649-00 Eval Board

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Analog Devices, upon request.